

/ Descriptions

WR0<5 M M E QSQ Æ M ı s ll 1 Silicon NPN transistor in a TO-92 Plastic Package.

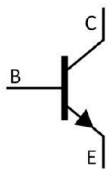
/ Features

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High transition frequency, low output capacitance.

/ Applications

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RF amplifier applications.

/ Equivalent Circuit



/ Pinning



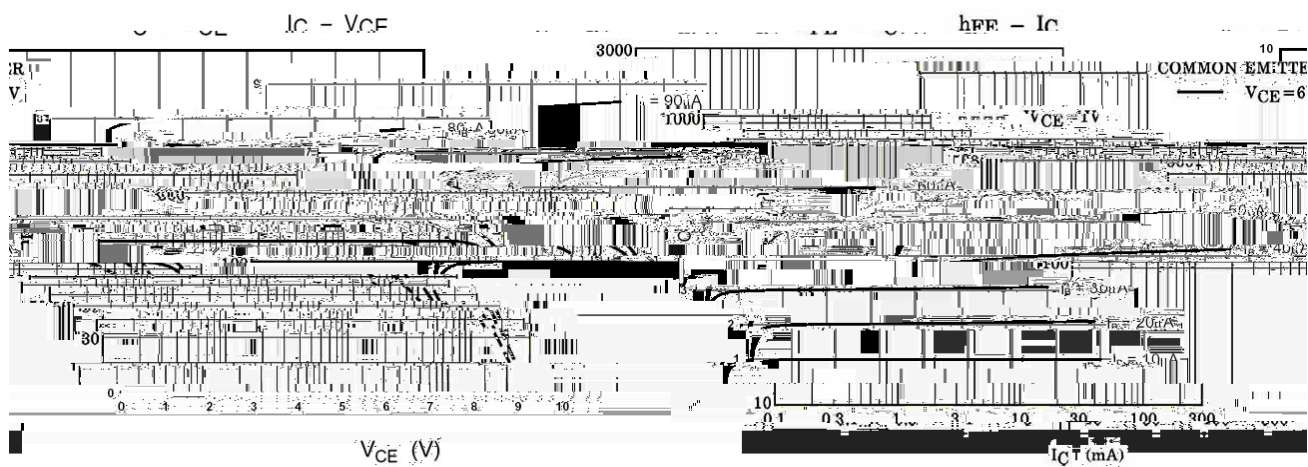
PIN1 χ Base PIN 2 χ Collector PIN 3 χ Emitter

/ hFE Classifications & Marking

h _{FE} Classifications Symbol	R	O	Y
h _{FE} Range	40~80	70~140	120~240

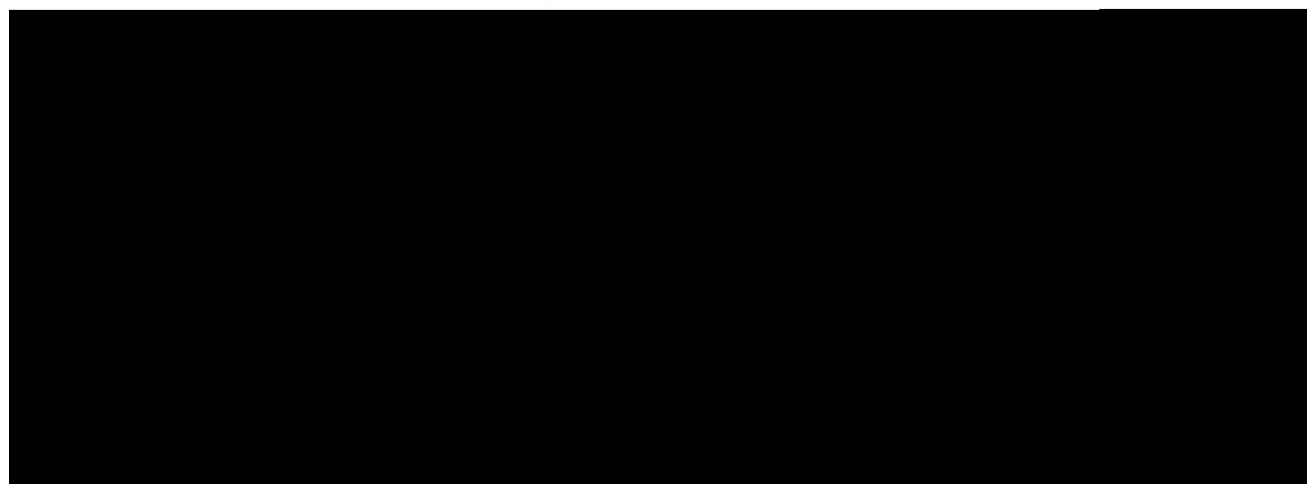
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	30	V
Collector to Emitter Voltage	V_{CEO}	20	V
Emitter to Base Voltage	V_{EBO}	4.0	V
Collector Current - Continuous	I_C		

Electrical Characteristic Curve

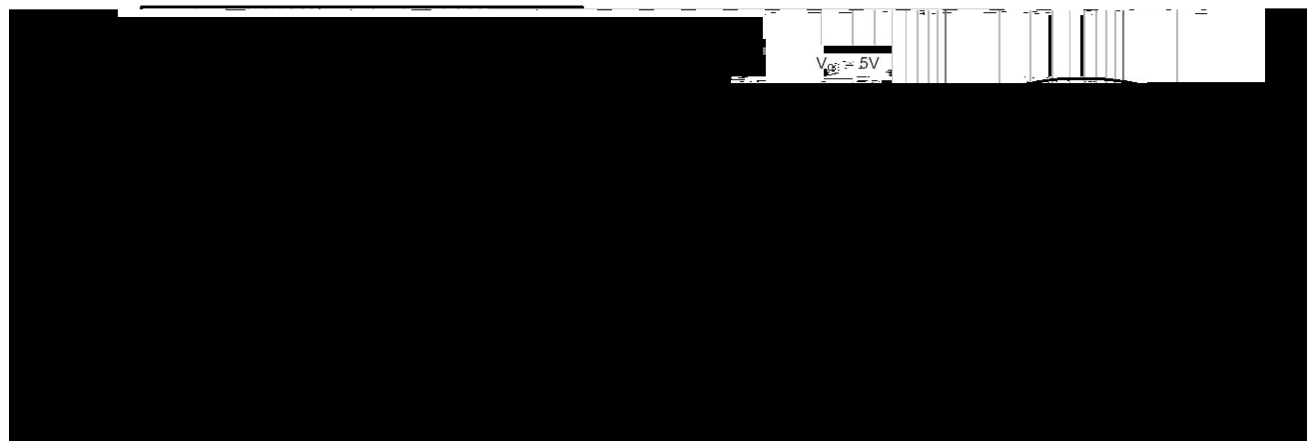


$V_{CE(sat)} - I_{C(sat)} = 10$

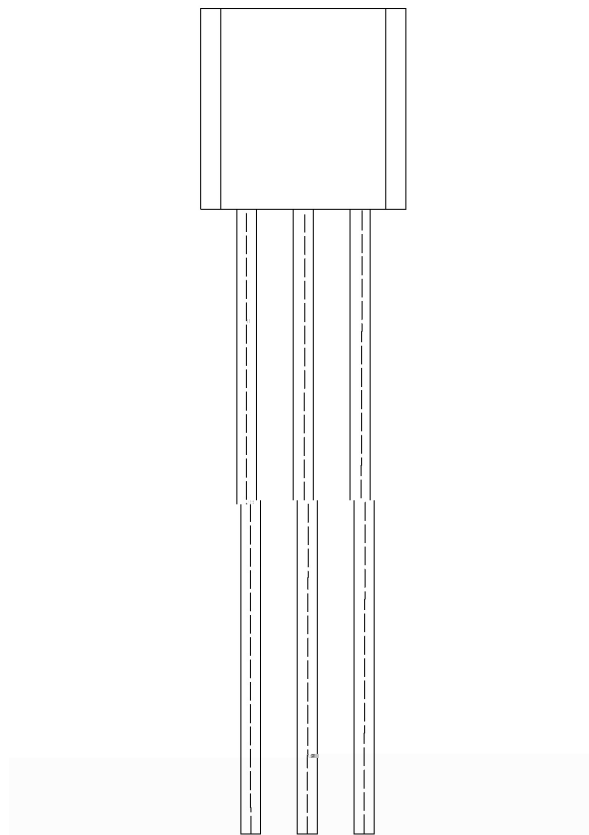
$C_{ob} - V_{CE} = 10$



$f_T - I_C$

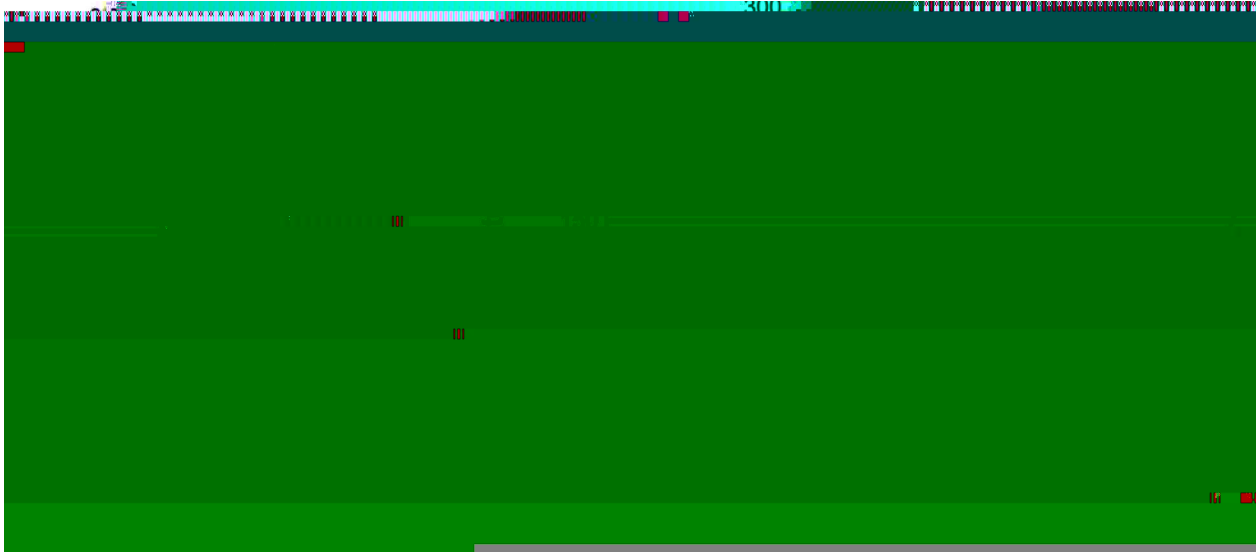


/ Marking Instructions


$$U =$$

h_{FE} Classifications Symbol.

() / Temperature Profile for Dip Soldering(Pb-Free)



б " X

1. 1. 25~150 °C, Time: 60~90sec;
2. 2. 255 °C, Duration: 5 ° 0.5sec;
3. 3. Cooling Speed: 2~10 ° /sec.

Note:

1. Preheating: 25~150 °C, Time: 60~90sec.
2. Peak Temp.: 255 °C, Duration: 5 ° 0.5sec.
3. Cooling Speed: 2~10 ° /sec.

/ Resistance to Soldering Heat Test Conditions

□ °C 270 ± 5 °C, Time: 10 ± 1 sec. Temp: 270 ± 5 °C Time: 10 ± 1 sec

/ Packaging SPEC.

“Q” T Y E / BULK

Package Type	Units					Dimension (unit mm3)		
	Units/Bag /	Bags/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Bag	Inner Box	Outer Box
TO-92	1,000	10	10,000	5	50,000	135×190	237×172×102	560×245×195
	1,000	10	10,000	10	100,000	135×190	237×172×102	560×245×375

“A” V Y E / AMMO

Package Type	Units					Dimension (unit mm3)	
	Units/tape /	Tape/Inner Box /	Rows/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Inner Box	Outer Box
TO-92	3,000	1	120	10	30,000	328×230×42	480×346×235 547×407×268

/ Notices